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	Application No.	Applicant(s)	
Nation of Allerta billion	10/602,721	MOULI ET AL.	
Notice of Allowability	Examiner	Art Unit	
	Eugene Lee	2815	
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included nerewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.			
1. This communication is responsive to <u>9/27/05</u> .			
2. X The allowed claim(s) is/are <u>1-10,12-33,35-37 and 59-65</u> .			
a.			
Attachment(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. ⊠ Examiner's Stateme	(PTO-413), te nent/Comment ent of Reasons for Allo	wance
		EUGENE L	.EE 12815

DETAILED ACTION

Allowable Subject Matter

- 1. Claims 1 thru 10, 12 thru 33, 35 thru 37, and 59 thru 65 are allowed.
- The following is an examiner's statement of reasons for allowance: The references of record, either singularly or in combination, do not teach or suggest at least a **pixel cell** comprising: a gate of a transistor formed at least partially **below** a surface of the substrate, the gate having a bottom surface below the surface of the substrate; a **photo-conversion device** formed **adjacent** to the gate, a doped surface layer of a first conductivity type, and a doped region of a second conductivity type underlying the doped surface layer, wherein the **second conductivity type layer is at a level below the level of the bottom surface of the gate**.

 Fossum 5,055,900 discloses a gate below a surface of the substrate, and a doped surface layer of a first conductivity type, however, Fossum does not disclose the second conductivity type layer (which is underlying the doped surface layer) wherein the second conductivity type layer is at a level below the level of the bottom surface of the gate (claims 1-10, and 12-19).

Regarding claims 20-23, the references of record, either singularly or in combination, do not teach or suggest at least a **pixel cell** comprising: a trench in the substrate; a gate of a transistor at least partially in the trench; a **photo-conversion device** formed **adjacent** to the gate, a doped surface layer of a first conductivity type below the surface of the substrate, and a doped region of a second conductivity type underlying the doped surface layer of a first conductivity type, wherein the **second conductivity type layer is at a level below the level of the bottom surface of the gate**.

Regarding claims 24-33, and 35-37, the references of record, either singularly or in combination, do not teach or suggest at least an imager system comprising: a pixel comprising: a gate of a transistor formed at least partially **below** a surface of the substrate, the gate having a bottom surface below the surface of the substrate; a **photo-conversion device** formed **adjacent** to the gate, a doped surface layer of a first conductivity type, and a doped region of a second conductivity type underlying the doped surface layer, wherein the **second conductivity type** layer is at a level below the level of the bottom surface of the gate.

Regarding claims 59-65, the references of record, either singularly or in combination, do not teach or suggest at least a pixel cell comprising: a trench; a gate of a transistor formed in the trench, the gate having a bottom surface below the surface of the substrate; a **photo-conversion** device formed adjacent to the gate, a doped surface layer of a first conductivity type, and a doped region of a second conductivity type underlying the doped surface layer, wherein the second conductivity type layer is at a level below the level of the bottom surface of the gate.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

INFORMATION ON HOW TO CONTACT THE USPTO

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Eugene Lee whose telephone number is 571-272-1733. The examiner can normally be reached on M-F 8-5.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on 571-272-1664. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Eugene Lee June 20, 2005

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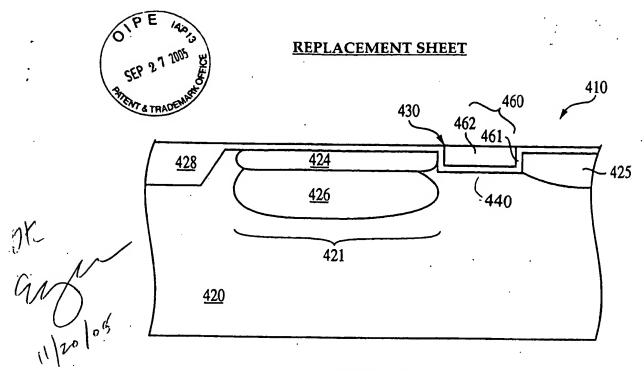


FIG. 4

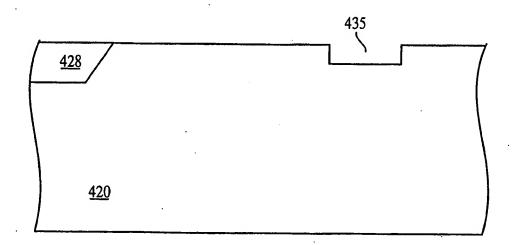


FIG. 5A